Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	34	(("4374116") or ("4119706") or ("3857927") or ("6362086") or ("5751025") or ("4139658") or ("5693578") or ("5880041") or ("5851892") or ("5840368") or ("5786263") or ("6239041") or ("6037273") or ("20010042344") or ("5959329")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 13:59
L3	1524363	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:00
L4	1379	3 and ((oxygen with hydrogen) same catal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:14
L5	990	4 and (wafer substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:05
L6	643	5 and (furnace chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:05
L7	71	6 and (wet adj2 oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:08
L8	70	7 and (water moisture vapor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:07
L9	70	8 and ((thermal wet) adj2 oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:09
L10	70	8 and ((thermal wet) near3 oxid$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:10

L11	60	8 and (((thermal wet) near3 oxid$5) with silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:12
L12	40	8 and ((((thermal wet) near3 oxid$5) with silicon) same temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:12
L13	465	3 and (((oxygen with hydrogen) same catal$4) same temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:19
L14	28	12 and 13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:15
L15	1261	3 and ((oxygen with hydrogen) same temperature same (water moisture))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:21
L16	226	3 and ((oxygen with hydrogen) same temperature same (water moisture) same catal$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:22
L17	69	16 and ((chamber furnace) with oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:23
L18	54	16 and ((chamber furnace) with oxidation with (wafer substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 14:23

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	34	(("4374116") or ("4119706") or ("3857927") or ("6362086") or ("5751025") or ("4139658") or ("5693578") or ("5880041") or ("5851892") or ("5840368") or ("5786263") or ("6239041") or ("6037273") or ("20010042344") or ("5959329")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 09:48
S2	2348	438/773,770,787,935,431,437. CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:33
S3	203	S2 and (wet adj oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 10:33
S4	59	S2 and ((wet adj oxidation) with water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 10:07
S5	9	S4 and (plurality near3 wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 10:26
S6	1	S5 and (gas$6 with moisture)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 10:08
S7	20	S3 and (plurality near3 wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 10:27
S8	130	S3 and (thermal near3 oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 10:34
S9	70	S8 and chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 10:35

S10	100	S8 and (furnace chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 10:35
S11	21	S10 and (first adj2 temperature) and (second adj2 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:07
S12	88	S10 and (oxidation near3 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:08
S13	59	S10 and ((moisture water wet) near3 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:09
S14	58	S12 and ((moisture water wet) near3 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:13
S15	28	S14 and (oxygen with hydrogen with catalyst)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:10
S16	38	S2 and (oxygen with hydrogen with catalyst)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:50
S17	11627	(oxygen with hydrogen with catalyst)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:50
S18	2096	(oxygen with hydrogen with catalyst with temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:58
S19	444	(oxygen with hydrogen with catalyst with temperature with (moisture water))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:52

S20	22	S19 and ((wet adj oxidation) with wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:55
S21	23	S19 and ((wet adj oxidation) same wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:56
S22	27	S18 and ((wet adj oxidation) same wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:59
S23	2171	(oxygen with hydrogen with (platinum Pt catalyst) with temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 11:58
S24	27	S23 and ((wet adj oxidation) same wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:36
S25	750	S23 and (oxygen with hydrogen with (water moisture))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:38
S26	6013	((oxygen with hydrogen with (water moisture)) same catal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:39
S27	1588	S26 and (wafer substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:41
S28	1327	S27 and ((thermal wet) oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:40
S29	348	((oxygen with hydrogen with (water moisture)) same catal$4 same (wafer substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:42

S30	126	((oxygen with hydrogen with (water moisture)) same catal$4 same (wafer substrate) same (oxide oxidation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:43
S31	112	S30 and temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:47
S32	85	S31 not peroxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:50
S33	63	semiconductor and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 12:53